

# PSMN7R0-100PS

N-channel 100V 6.8 mΩ standard level MOSFET in TO220

Rev. 02 — 7 January 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175°C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	<a href="#">[1]</a>	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	269	W
$T_j$	junction temperature		-55	-	175	°C
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C};$ $I_D = 100\text{ A}; V_{sup} = 100\text{ V};$ unclamped; $R_{GS} = 50\text{ }\Omega$	-	-	315	mJ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 50\text{ V};$ see <a href="#">Figure 14</a> and <a href="#">17</a>	-	36	-	nC
$Q_{G(\text{tot})}$	total gate charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 50\text{ V};$ see <a href="#">Figure 17</a> and <a href="#">14</a>	-	125	-	nC



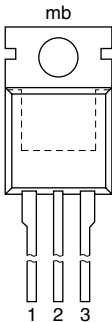
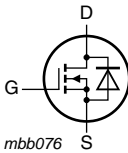
**Table 1. Quick reference ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <a href="#">Figure 12</a>	-	-	12	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 13</a>	-	5.4	6.8	mΩ

[1] Continuous current is limited by package

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78 (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
PSMN7R0-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

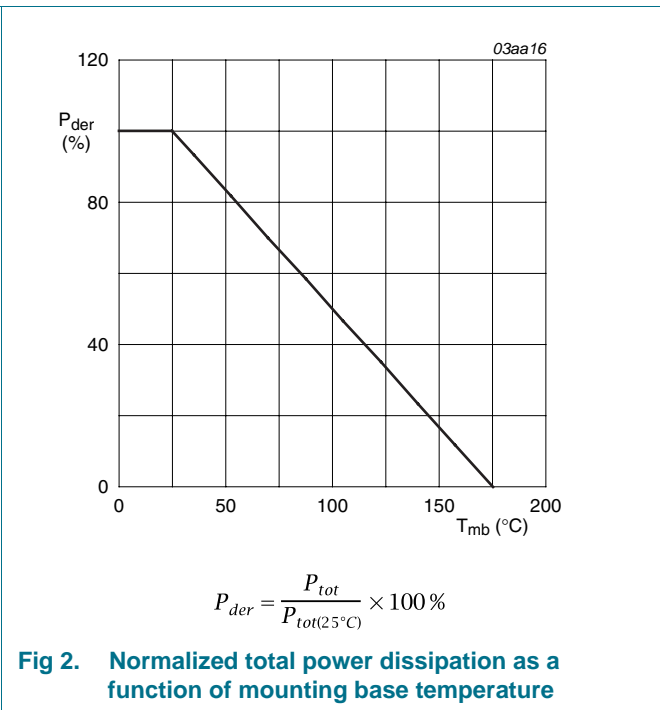
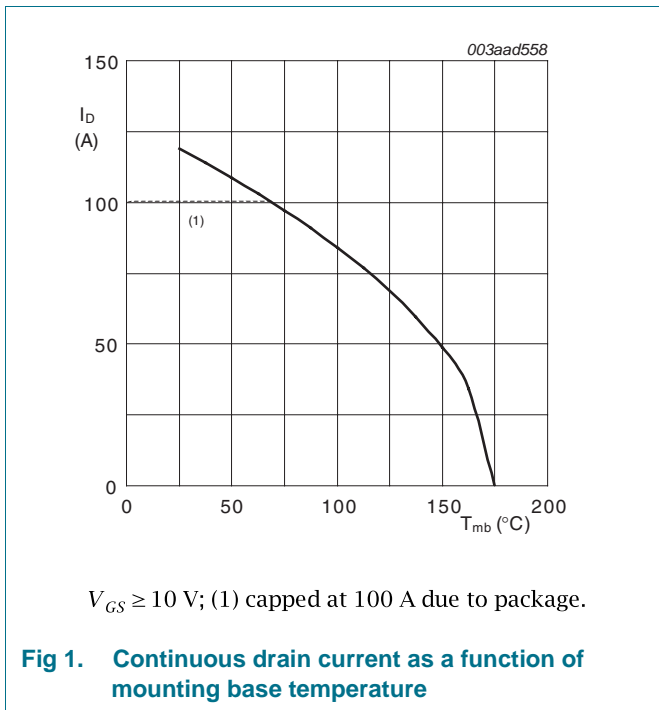
### 4. Limiting values

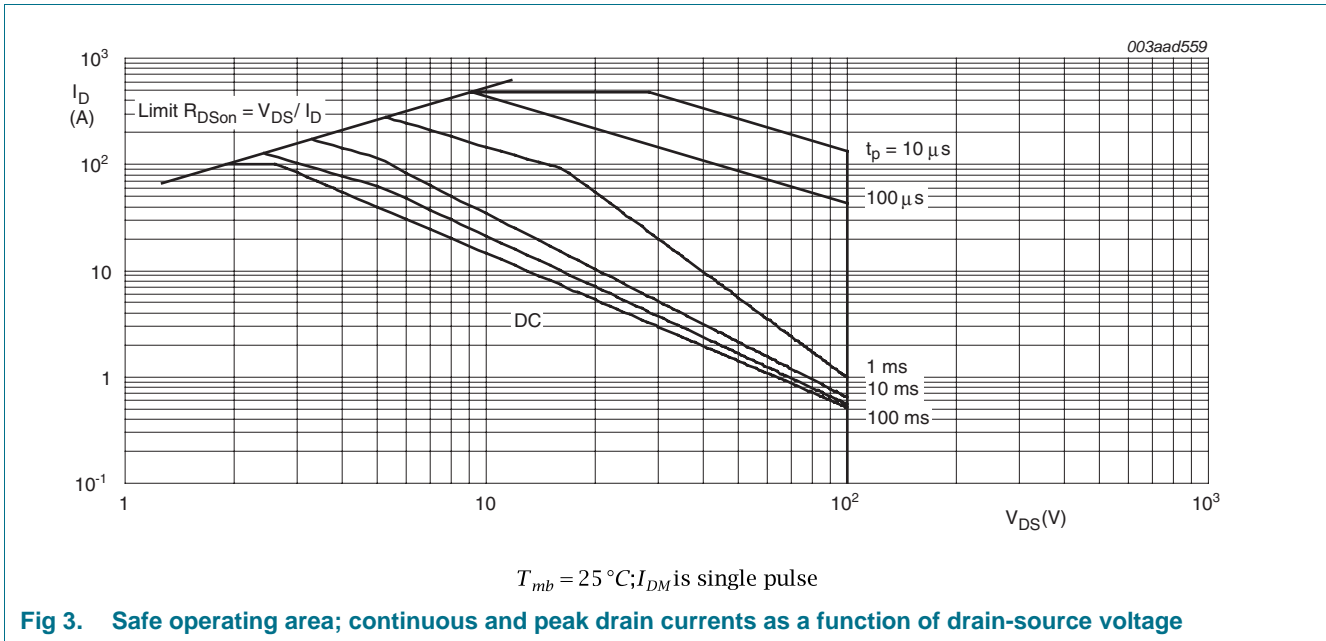
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≤ 175 °C; T <sub>j</sub> ≥ 25 °C; R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a>	-	85	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a> [1]	-	100	A
I <sub>DM</sub>	peak drain current	t <sub>p</sub> ≤ 10 μs; pulsed; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 3</a>	-	475	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	269	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>slid(M)</sub>	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C; [1]	-	100	A
I <sub>SM</sub>	peak source current	t <sub>p</sub> ≤ 10 μs; pulsed; T <sub>mb</sub> = 25 °C	-	475	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 100 A; V <sub>sup</sub> = 100 V; unclamped; R <sub>GS</sub> = 50 Ω	-	315	mJ

[1] Continuous current is limited by package





### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.3	0.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

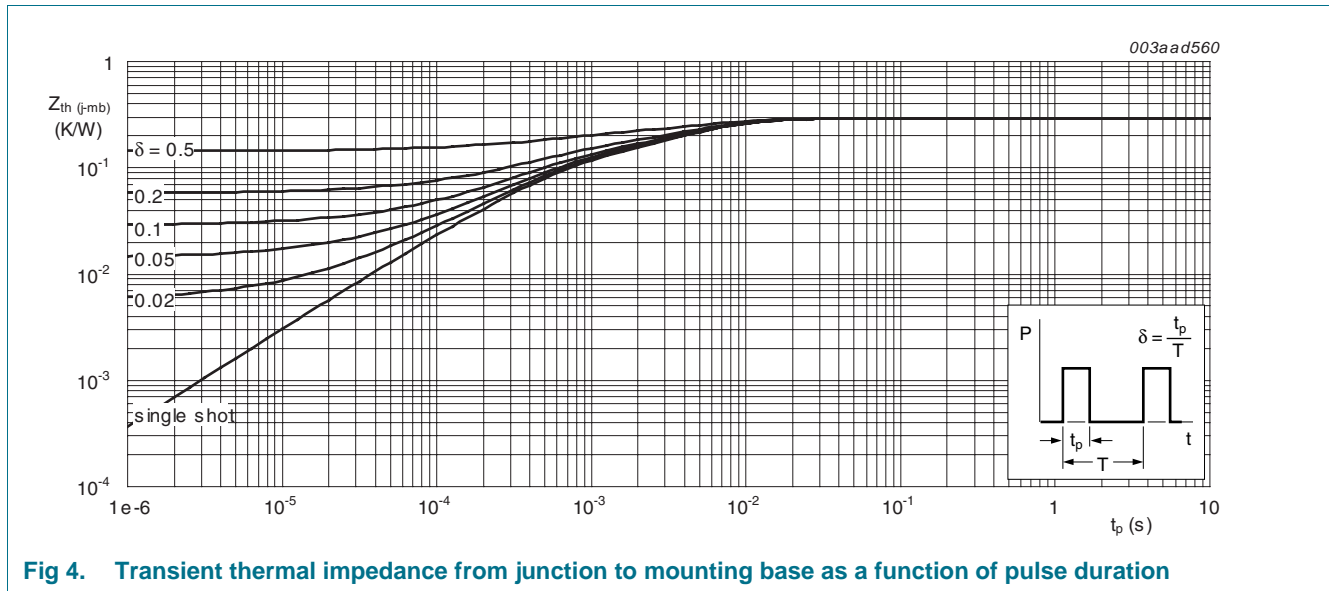


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

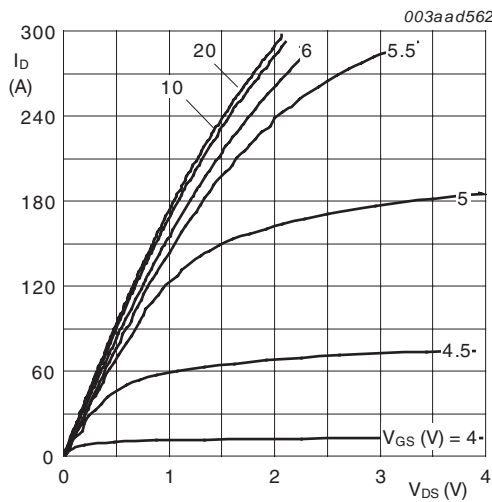
## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a> and <a href="#">10</a>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	-	-	4.6	V
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	150	$\mu\text{A}$
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.08	5	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	-	12	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	15	19	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	5.4	6.8	mΩ
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	0.74	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 17</a> and <a href="#">14</a>	-	125	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	100	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> and <a href="#">17</a>	-	28	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a>	-	19.4	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	9	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> and <a href="#">17</a>	-	36	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 50 \text{ V};$ see <a href="#">Figure 14</a> and <a href="#">17</a>	-	4.3	-	V
$C_{iss}$	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	6686	-	pF
$C_{oss}$	output capacitance		-	438	-	pF
$C_{rss}$	reverse transfer capacitance		-	272	-	pF

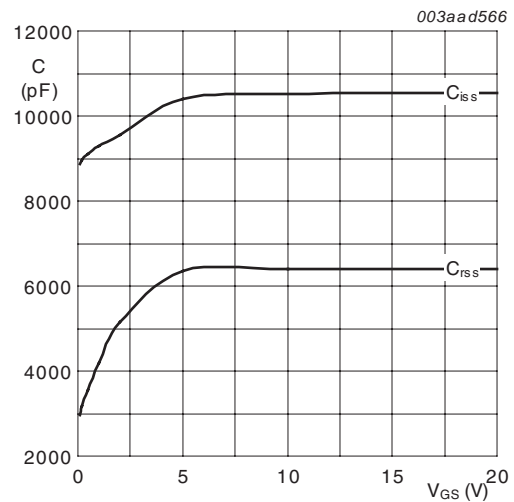
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50\text{ V}; R_L = 2\ \Omega; V_{GS} = 10\text{ V};$	-	34.6	-	ns
$t_r$	rise time	$R_{G(ext)} = 4.7\ \Omega; T_j = 25\text{ }^\circ\text{C}$	-	45.6	-	ns
$t_{d(off)}$	turn-off delay time		-	103.9	-	ns
$t_f$	fall time		-	49.5	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}; di_S/dt = 100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	64	-	ns
$Q_r$	recovered charge	$V_{DS} = 50\text{ V}$	-	167	-	nC



$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



$V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

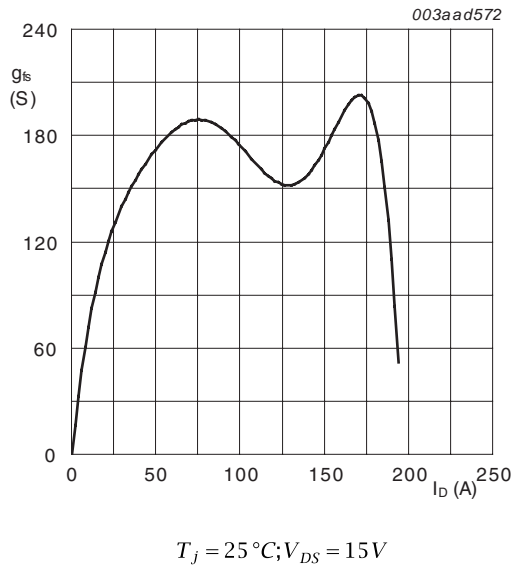


Fig 7. Forward transconductance as a function of drain current; typical values

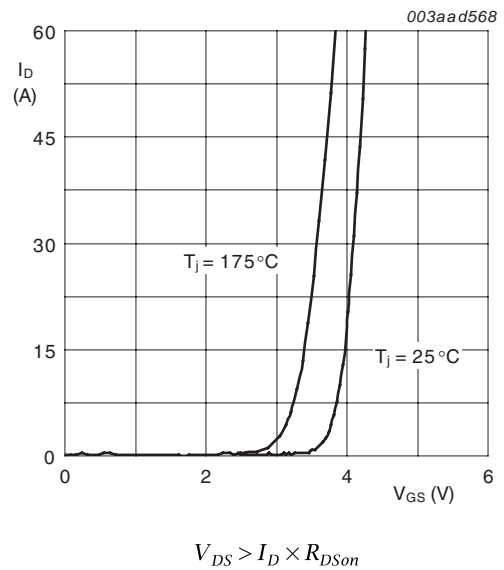


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

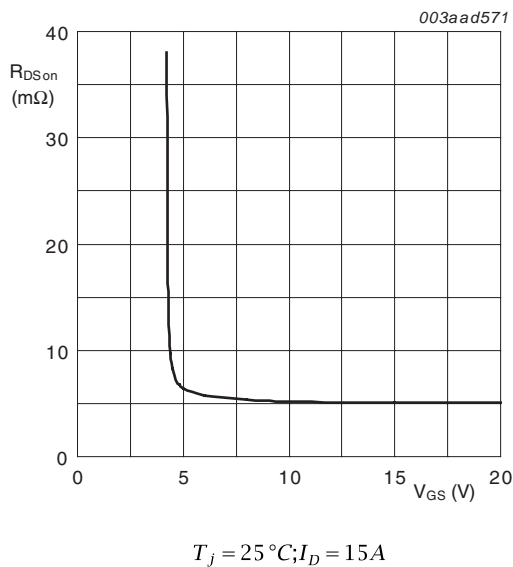


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

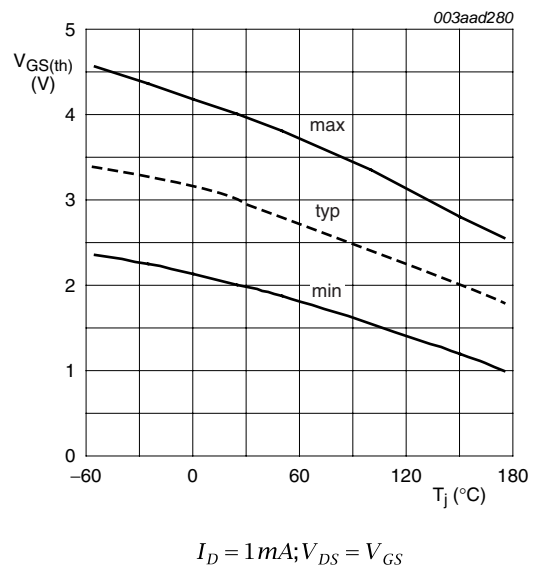
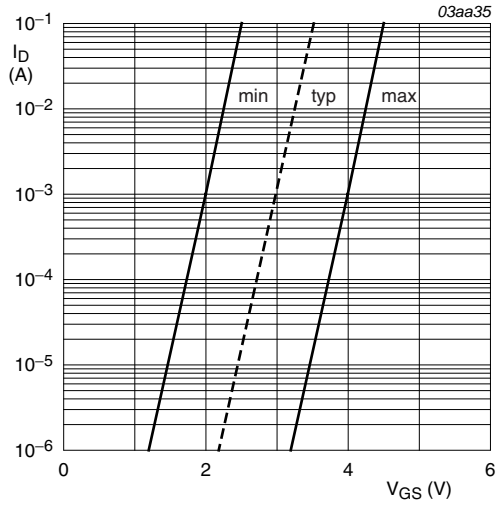


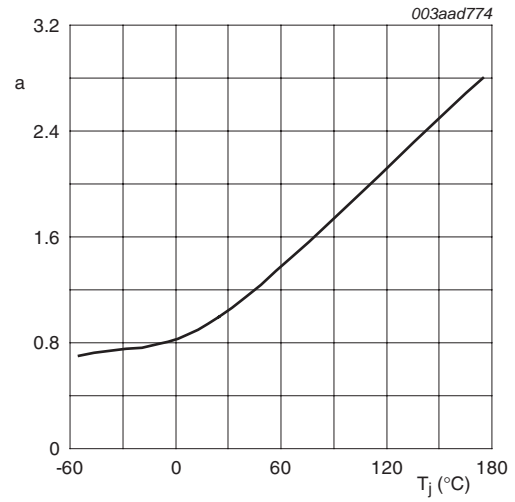
Fig 10. Gate-source threshold voltage as a function of junction temperature





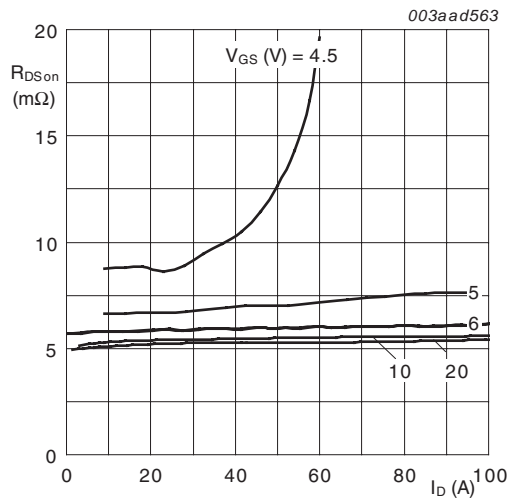
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25\text{ }^\circ\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25\text{ }^\circ\text{C}$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

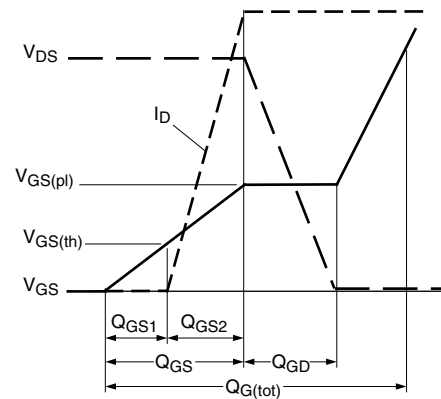
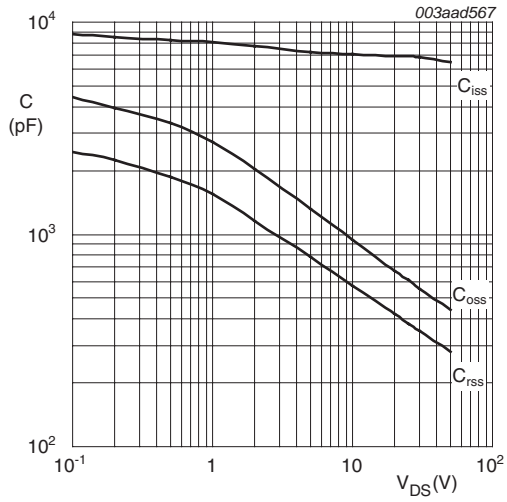
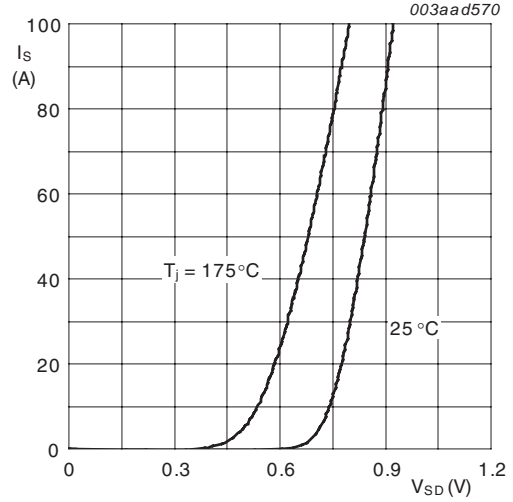


Fig 14. Gate charge waveform definitions



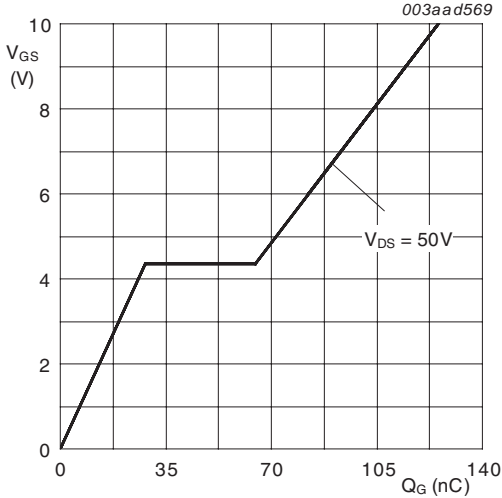
$V_{GS} = 0V; f = 1MHz$

**Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$V_{GS} = 0V$

**Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



$$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$$

Fig 17. Gate-source voltage as a function of gate charge; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

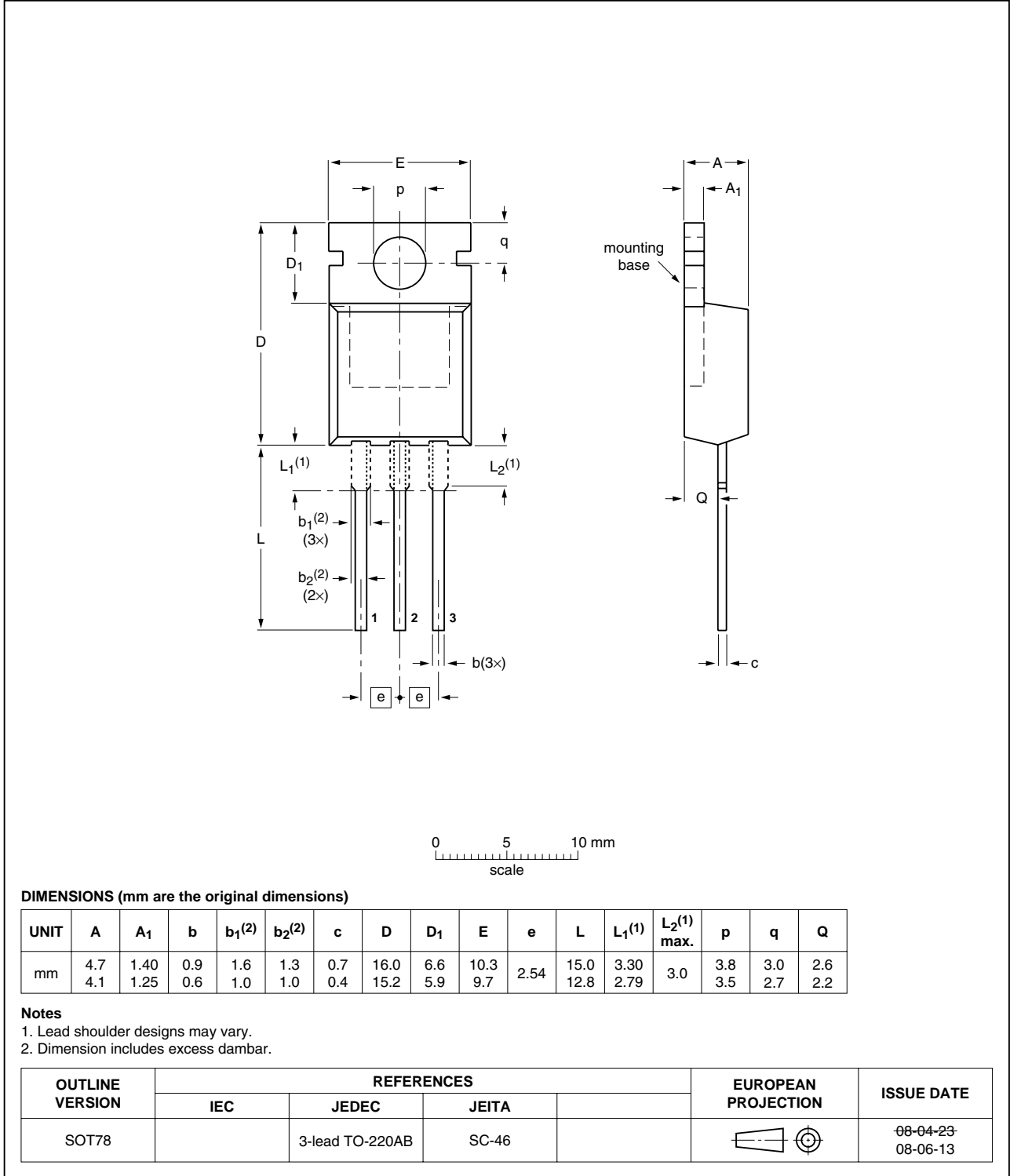


Fig 18. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-100PS_2	20100107	Product data sheet	-	PSMN7R0-100PS_1
Modifications:	• Status changed from objective to product.			
PSMN7R0-100PS_1	20090917	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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